

### TIP140F/141F/142F

### Monolithic Construction With Built In Base-Emitter Shunt Resistors

- Complement to TIP145F/146F/147F
- High DC Current Gain :  $h_{FE} = 1000 @ V_{CE} = 4V, I_{C} = 5A (Min.)$
- Industrial Use

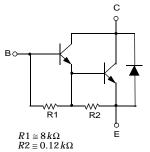


## **NPN Epitaxial Darlington Transistor**

### Absolute Maximum Ratings T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage : TIP140F	60	V
	: TIP141F	80	V
	: TIP142F	100	V
	Collector-Emitter Voltage : TIP140F	60	V
$V_{CEO}$	: TIP141F	80	V
	: TIP142F	100	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current (DC)	10	Α
I <sub>CP</sub>	Collector Current (Pulse)	15	Α
I <sub>B</sub>	Base Current (DC)	0.5	Α
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	60	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 65 ~ 150	°C





## Electrical Characteristics $\rm T_{C} = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V <sub>CEO</sub> (sus)	Collector-Emitter Sustaining Voltage : TIP140F : TIP141F : TIP142F	I <sub>C</sub> = 30mA, I <sub>B</sub> = 0	60 80 100			V V V
I <sub>CEO</sub>	Collector Cut-off Current : TIP140F : TIP141F : TIP142F	$V_{CE} = 30V, I_{B} = 0$ $V_{CE} = 40V, I_{B} = 0$ $V_{CE} = 50V, I_{B} = 0$			2 2 2	mA mA mA
I <sub>CBO</sub>	Collector Cut-off Current : TIP140F : TIP141F : TIP142F	$V_{CB} = 60V, I_{E} = 0$ $V_{CB} = 80V, I_{E} = 0$ $V_{CB} = 100V, I_{E} = 0$			1 1 1	mA mA mA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{BE} = 5V, I_{C} = 0$			2	mA
h <sub>FE</sub>	DC Current Gain	$V_{CE} = 4V, I_{C} = 5A$ $V_{CE} = 4V, I_{C} = 10A$	1000 500			
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	$I_C = 5A, I_B = 10mA$ $I_C = 10A, I_B = 40mA$			2 3	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	$I_C = 10A, I_B = 40mA$			3.5	V
V <sub>BE</sub> (on)	Base-Emitter ON Voltage	$V_{CE} = 4V, I_{C} = 10A$			3	V
t <sub>D</sub>	Delay Time	$V_{CC} = 30V, I_{C} = 5A$		0.15		μs
t <sub>R</sub>	Rise Time	$I_{B 1} = 20 \text{mA}, I_{B2} = -20 \text{mA}$		0.55		μs
t <sub>STG</sub>	Storage Time	$R_L = 6\Omega$		2.5		μs
t <sub>F</sub>	Fall Time			2.5		μs

# **Typical Characteristics**

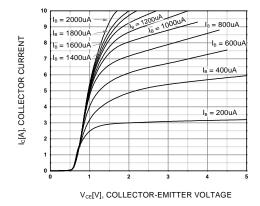


Figure 1. Static Characteristics

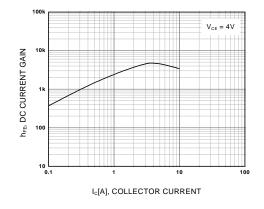


Figure 2. DC current Gain

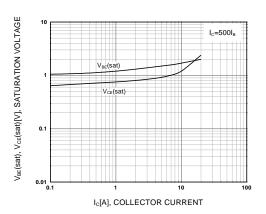


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

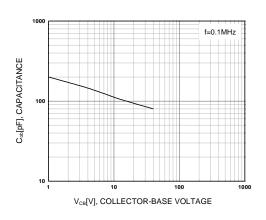


Figure 4. Collector Output Capacitance

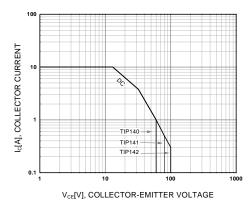


Figure 5. Safe Operating Area

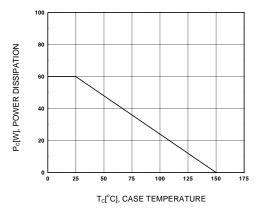


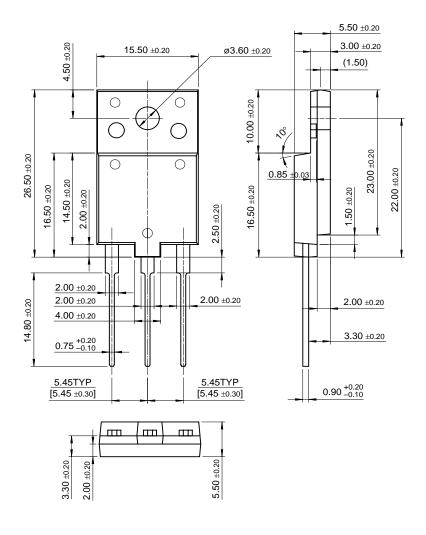
Figure 6. Power Derating

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# **Package Demensions**

# TO-3PF



Dimensions in Millimeters

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